Thyristor Diode Modules

Liujing rectifier co., Ltd.

V_{RSM}	V_{RRM} V_{DRM}	I_{TRMS} =440A(maximum value for continous operation)		
V	V	I_{TAV} =280A(sin.180; Tc=79℃)		
2100	2000	SKKT 280/20E H4	SKKH 280/20E H4	
2300	2200	SKKT 280/22E H4	SKKH 280/22E H4	

Symbol	Conditions	Values	Units
I_{TAV}	sin. 180; Tc = 79 (85)℃;	280 (252)	A
I_{TSM}	T_{vj} = 25℃; 10ms	8500	A
	T_{vj} = 125℃; 10ms	7500	A
i^2t	T_{vj} = 25℃; 8，3 ...10ms	361000	A^2S
	T_{vj} = 125℃; 8，3 ...10ms	281000	A^2S
V_T	T_{vj} = 25℃; I_T=840A	max. 1.55	V
$V_{T(TO)}$	T_{vj} = 125℃	max. 0.9	V
r_T	T_{vj} = 125℃	max. 0.75	mΩ
I_{DD};I_{RD}	T_{vj} = 125℃; V_{RD}=V_{RRM} ; V_{DD}=V_{DRM}	max. 60	mA
t_{gd}	T_{vj} = 25℃; I_G = 1A; di$_G$/dt = A/μs	1	μs
t_{gr}	V_D = 0.67*V_{DRM}	2	μs
$(di/dt)_{cr}$	T_{vj} = 125℃	max. 250	A/μs
$(dv/dt)_{cr}$	T_{vj} = 125℃	max. 1000	V/μs
t_q	T_{vj} = 125℃ ,typ	250	μs
I_H	T_{vj} = 25℃ ; typ./max	150 / 500	mA
I_L	T_{vj} = 25℃ ; RG = 33Ω ; typ./max	300 / 2000	mA
V_{GT}	T_{vj} = 25℃ ; d.c.	min. 3	V
I_{GT}	T_{vj} = 25℃ ; d.c.	min. 200	mA
V_{GD}	T_{vj} = 125℃ ; d.c.	max. 0.25	V
I_{GD}	T_{vj} = 125 ℃ ; d.c.	max. 10	mA
$R_{th(j-c)}$	cont.; per thyristor/per module	0.11 / 0.055	K/W
$R_{th(j-c)}$	sin. 180; per thyristor/per module	0.116 / 0.058	K/W
$R_{th(j-c)}$	rec. 120; per thyristor/per module	0.13 / 0.065	K/W
$R_{th(j-c)}$	per thyristor/per module	0.04 / 0.02	K/W
T_{vj}		- 40...+ 125	℃
T_{stg}		- 40...+ 125	℃
V_{isol}	a. c. 50Hz; r.m.s. ; 1s/1min	4800 / 4000	V~
M_s	to heatsink	9 ± 15%[1])	Nm
M_t	to terminal	9 ± 15%[2])	Nm
a		5 * 9.81	m/s^2
m	approx.	600	g
Case	SKKH	LJ3	

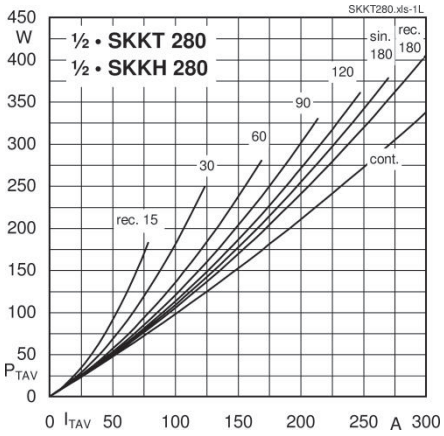


Fig. 1L Power dissipation per thyristor vs. on-state current

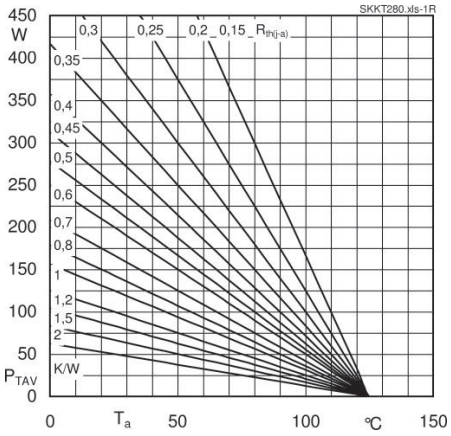


Fig. 1R Power dissipation per thyristor vs. ambient temp.

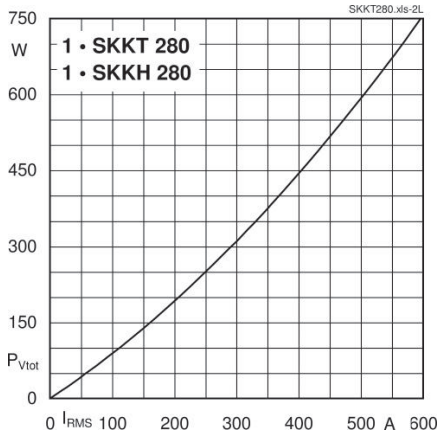


Fig. 2L Power dissipation per module vs. rms current

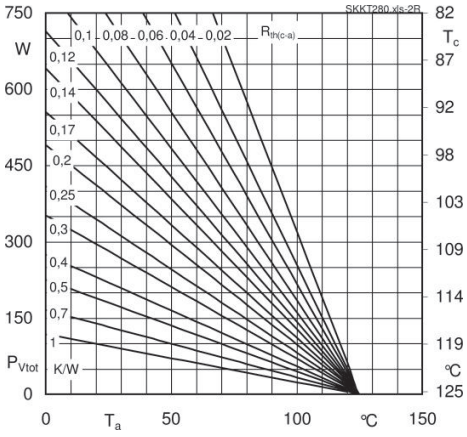


Fig. 2R Power dissipation per module vs. case temp.

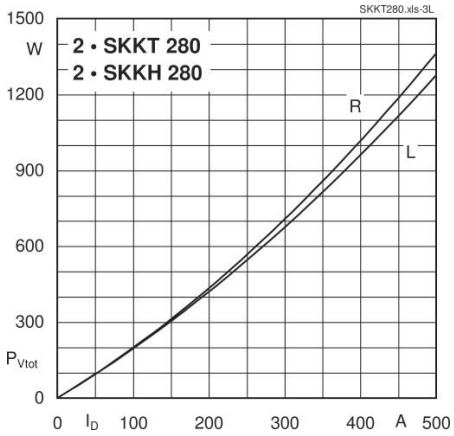


Fig. 3L Power dissipation of two modules vs. direct current

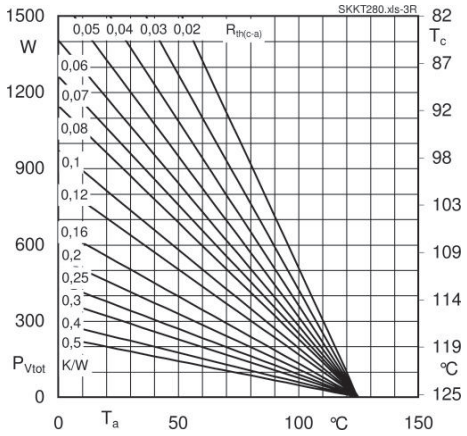


Fig. 3R Power dissipation of two modules vs. case temp.

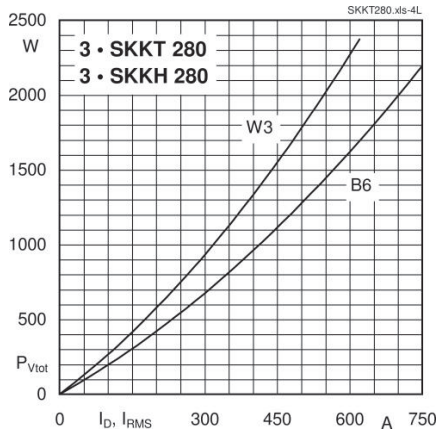


Fig. 4L Power dissipation of three modules vs. direct and rms current

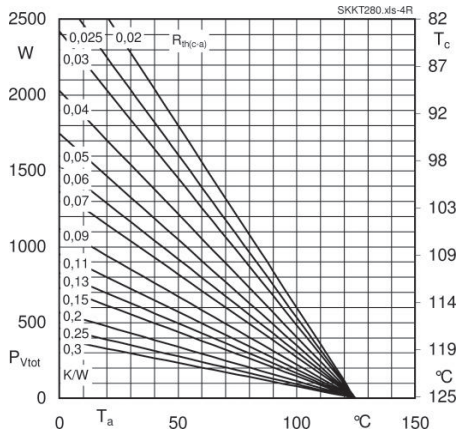


Fig. 4R Power dissipation of three modules vs. case temp.

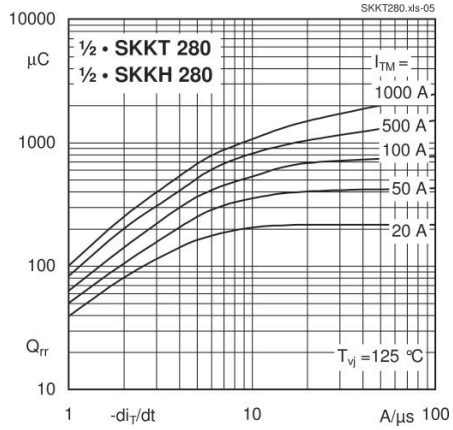


Fig. 5 Recovered charge vs. current decrease

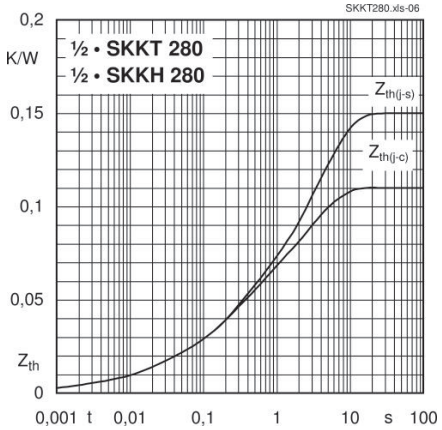


Fig. 6 Transient thermal impedance vs. time

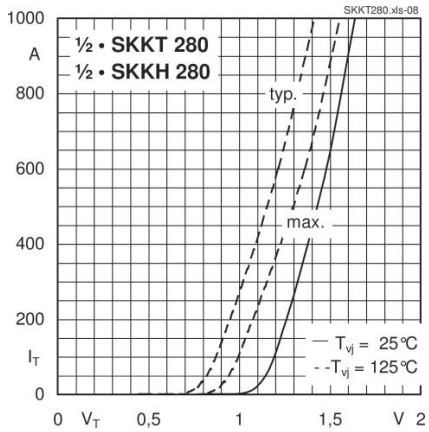


Fig. 7 On-state characteristics

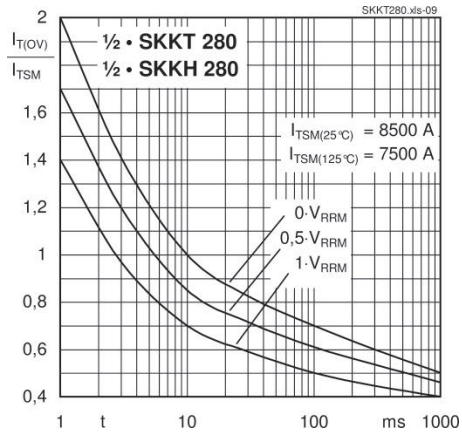
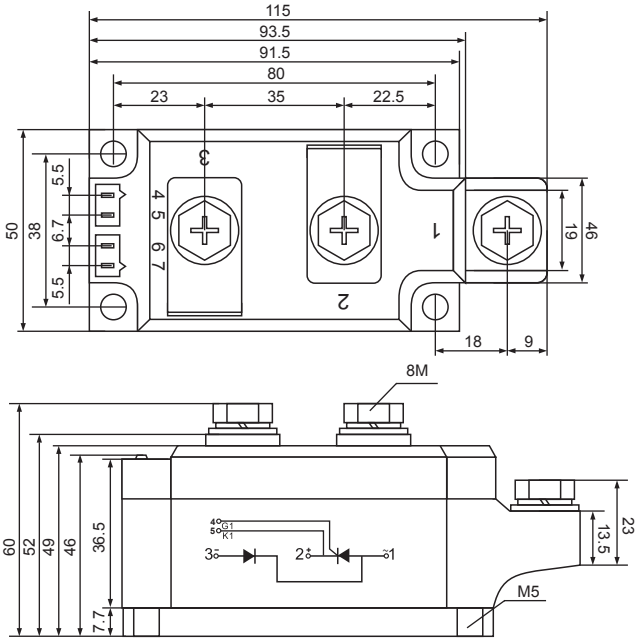


Fig. 8 Surge overload current vs. time



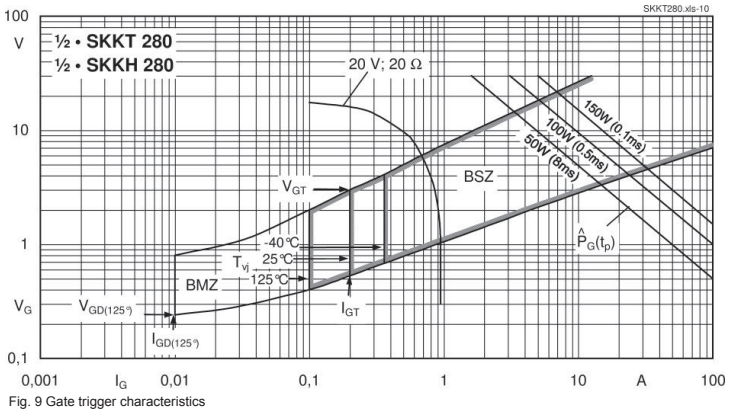


Fig. 9 Gate trigger characteristics

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